

SI2301BDS-T1-GE3 P-Channel 20-V (D-S) MOSFET

MOSFET PRODUCT SUMMARY					
V _{DS} (V)	R_{DS(on)} (Ω)	I _D (A) ^a	Q _g (Typ.)		
	0.035 at V _{GS} = - 10 V	- 5 ^e			
- 20	0.043 at V _{GS} = - 4.5 V	- 5 ^e	10 nC		
	0.061 at V _{GS} = - 2.5 V	- 4.8			

G 1

S 2

TO-236 (SOT-23)

3 D

FEATURES

- Halogen-free According to IEC 61249-2-21
 Definition
- TrenchFET[®] Power MOSFET
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC

APPLICATIONS

- · Load Switch
- PA Switch
- DC/DC Converters

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)						
Parameter	Symbol	Limit	Unit			
Drain-Source Voltage	V _{DS}	- 20	V			
Gate-Source Voltage	V _{GS}	± 12	v			
	T _C = 25 °C		- 5 ^e			
Continuous Drain Current (T ₁ = 150 °C)	T _C = 70 °C	I _D	- 4.8			
	T _A = 25 °C	U	- 4.5 ^{b, c}			
	T _A = 70 °C		- 3.5 ^{b, c}	A		
Pulsed Drain Current	I _{DM}	- 18				
Continuous Source-Drain Diode Current	T _C = 25 °C	I _S	- 2.1			
Continuous Source-Drain Diode Guirent	T _A = 25 °C	'8	- 1.0 ^{b, c}			
	T _C = 25 °C		2.5			
Maximum Power Dissipation	T _C = 70 °C	PD	1.6	w		
	T _A = 25 °C	- FD	1.25 ^{b, c}	vv		
	T _A = 70 °C		0.8 ^{b, c}	1		
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150	°C			

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^{b, d}	≤5 s	R _{thJA}	75	100	°C/W	
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	40	50	0/11	

Notes:

- a. Based on T_C = 25 °C.
- b. Surface mounted on 1" x 1" FR4 board.
- c. t = 5 s.
- d. Maximum under steady state conditions is 166 $^{\circ}\text{C/W}.$
- e. Package limited.

MOSFET SPECIFICATIONS Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit	
Static	Symbol			Typ.	Wax.		
Drain-Source Breakdown Voltage	V _{DS}	V _{DS} = 0 V, I _D = - 250 μA	- 20			V	
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$			- 13.4			
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	I _D = - 250 μA		2.9		mV/°C	
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \ \mu A$	- 0.5		- 1.5	V	
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 12 V$			± 100	nA	
	· .	V _{DS} = - 20 V, V _{GS} = 0 V	- 1		- 1	μΑ	
Zero Gate Voltage Drain Current	IDSS	$V_{DS} = -20 V, V_{GS} = 0 V, T_{J} = 55 °C$			- 10		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \leq$ - 5 V, V_{GS} = - 4.5 V	- 18			А	
		V _{GS} = - 10 V, I _D = - 5.1 A		0.035			
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 4.5 V, I _D = - 4.5 A		0.043		Ω	
		V _{GS} = - 2.5 V, I _D = - 3.7 A		0.061			
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 5 V, I _D = - 5.1 A		15		S	
Dynamic ^b						1	
Input Capacitance	C _{iss}			835		pF	
Output Capacitance	C _{oss}	V _{DS} = - 10 V, V _{GS} = 0 V, f = 1 MHz		180			
Reverse Transfer Capacitance	C _{rss}			155			
		$V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -5.1 \text{ A}$		10			
Total Gate Charge				6.4		nC	
Gate-Source Charge	Q _{gs}	V_{DS} = - 10 V, V_{GS} = - 2.5 V, I_{D} = - 5.1 A		1.7			
Gate-Drain Charge	Q _{gd}			3.4			
Gate Resistance	Rg	f = 1 MHz	0.9	4.4	8.8	Ω	
Turn-On Delay Time	t _{d(on)}			22	33		
Rise Time	t _r	V_{DD} = - 10 V, R_L = 2.4 Ω		20	30	- ns	
Turn-Off Delay Time	t _{d(off)}	I_D = - 4.1 A, V_{GEN} = - 4.5 V, R_g = 1 Ω		28	42		
Fall Time	t _f			9	18		
Drain-Source Body Diode Characteristi	cs						
Continuous Source-Drain Diode Current	۱ _S	T _C = 25 °C			- 2.1	A	
Pulse Diode Forward Current ^a	I _{SM}				- 20		
Body Diode Voltage	V _{SD}	I _S = - 4.1 A		- 0.8	- 1.2	V	
Body Diode Reverse Recovery Time	t _{rr}			23	35	ns	
Body Diode Reverse Recovery Charge	Q _{rr}			12	20	nC	
Reverse Recovery Fall Time	t _a	I _F = - 4.1 A, dl/dt = 100 A/μs, T _J = 25 °C		15			
Reverse Recovery Rise Time	t _b			8		ns	

Notes:

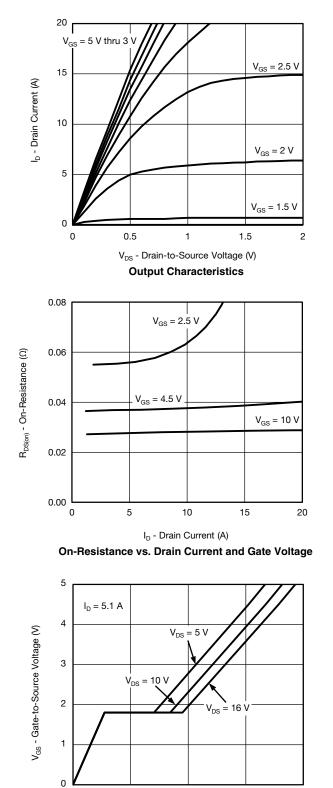
a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.

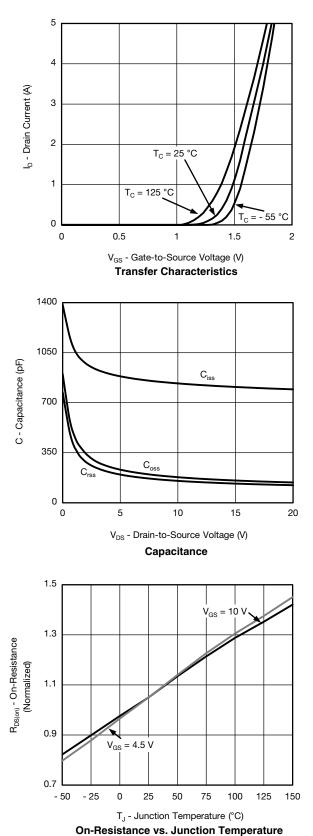
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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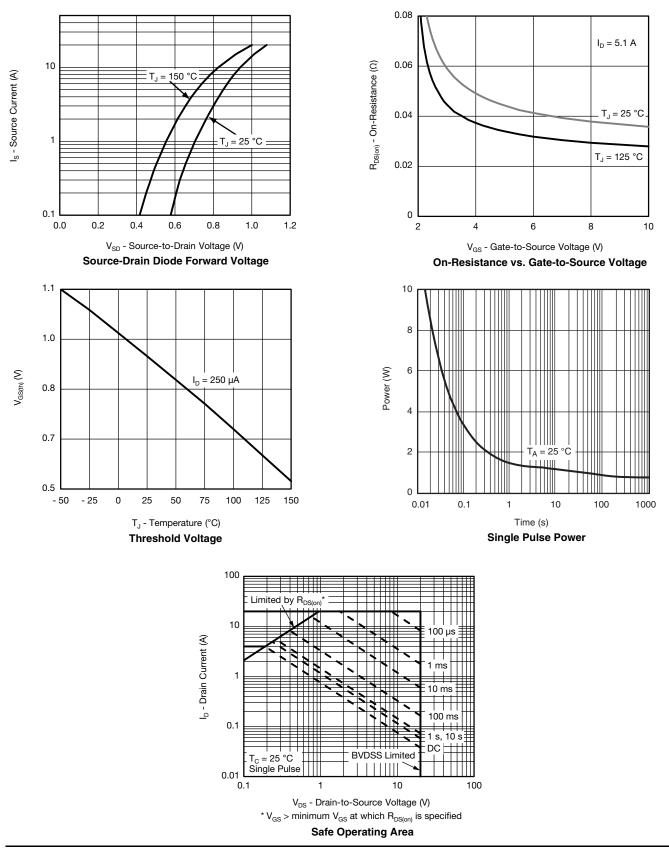
Q_q - Total Gate Charge (nC)

Gate Charge

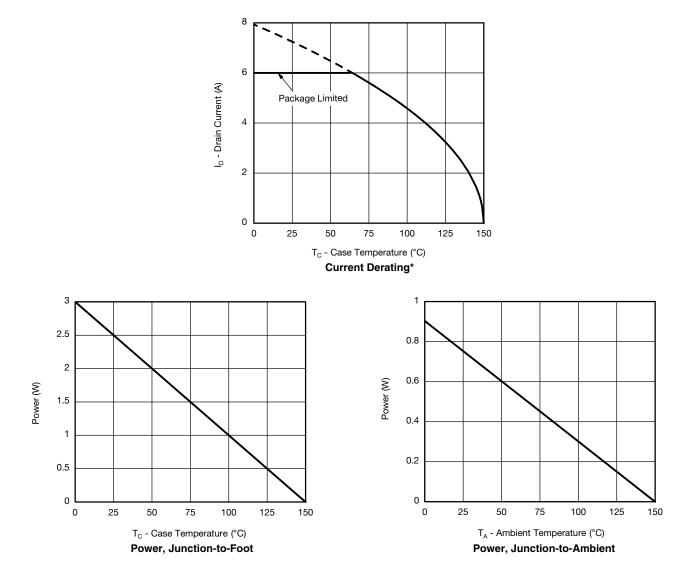
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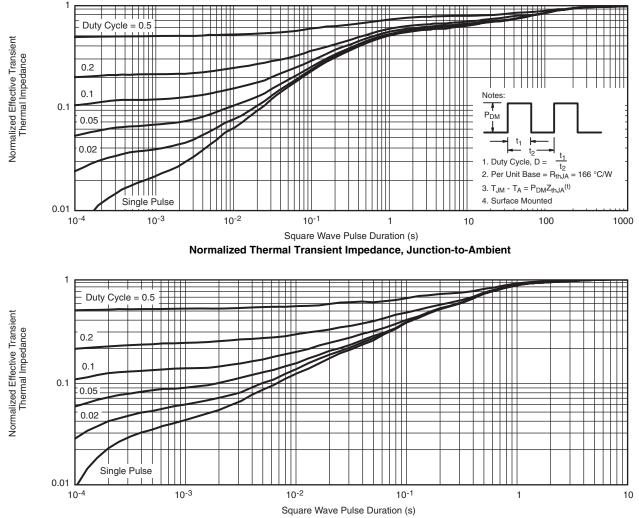






* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

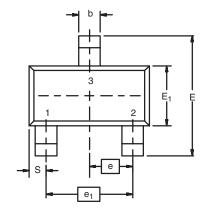


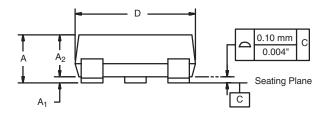


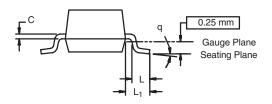
Normalized Thermal Transient Impedance, Junction-to-Foot



SOT-23 (TO-236): 3-LEAD







Dim	MILLIN	IETERS	INCHES		
	Min	Max	Min	Max	
Α	0.89	1.12	0.035	0.044	
A ₁	0.01	0.10	0.0004	0.004	
A ₂	0.88	1.02	0.0346	0.040	
b	0.35	0.50	0.014	0.020	
C	0.085	0.18	0.003	0.007	
D	2.80	3.04	0.110	0.120	
E	2.10	2.64	0.083	0.104	
E ₁	1.20	1.40	0.047	0.055	
е	0.95 BSC		0.0374 Ref		
e ₁	1.90) BSC	0.0748 Ref		
L	0.40	0.60	0.016	0.024	
L ₁	0.64 Ref		0.025 Ref		
S	0.50 Ref		0.020 Ref		
q	3°	8°	3°	8°	
ECN: S-03946-Rev. K, 09- DWG: 5479	Jul-01		<u>.</u>		

SI2301BDS-T1-GE3



RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads Dimensions in Inches/(mm)

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